

Docket No. 248520US2S

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yoshiaki FUKUZUMI

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: MAGNETIC MEMORY DEVICE HAVING A PLURALITY OF MAGNETO-RESISTANCE EFFECT ELEMENTS
ARRANGED IN A MATRIX FORM AND METHOD FOR MANUFACTURING THE SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☒ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION


- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



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LIST OF RELATED CASES

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>
242221US2RD	10/653,098	09/03/03	KAI et al.

DOCKET NO: 248520US2S

Sheet 1 of 1

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RESISTANCE EFFECT ELEMENTS ARRANGED IN A MATRIX FORM AND
METHOD FOR MANUFACTURING THE SAME

STATEMENT OF RELEVANCY

Reference AA (US 6,005,800) on Form PTO- 1449:

This Patent shows similar shape of TMR.

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

248520US2S

SERIAL NO.

New Application

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Yoshiaki FUKUZUMI

FILING DATE

Herewith

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,005,800	12/21/99	Roger Hilsen KOCH, et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", DIGEST OF TECHNICAL PAPERS, IEEE International Solid-State Circuits Conference, SESSION 7 / TD: EMERGING MEMORY & DEVICE TECHNOLOGIES, February 8, 2000, pgs. 128-129				
	AX	Masashige SATO, et al., "Spin-Valve-Like Properties of Ferromagnetic Tunnel Junctions", JPN. J. APPL. PHYS., Vol. 36 Part 2, No. 2B, February 15, 1997, pgs. L200-L201				
	AY					
	AZ					<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.